

**Product Summary**

| Symbol            | Value     | Unit |
|-------------------|-----------|------|
| $I_{T(RMS)}$      | 6         | A    |
| $V_{DRM} V_{RRM}$ | 600 / 800 | V    |
| $V_{TM}$          | 1.55      | V    |

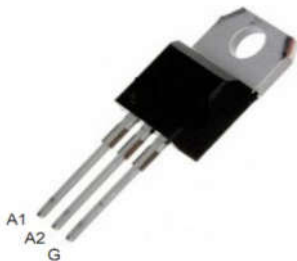
**Feature**

With high ability to withstand the shock loading of large current, With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

**Application**

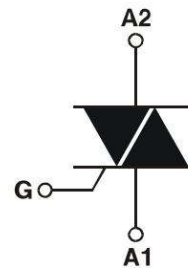
Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

**Package**

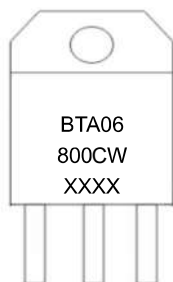


**TO-220A Insulated**

**Circuit diagram**



**Marking**



### Absolute maximum ratings (Ta=25°C unless otherwise noted)

| Parameter   | Symbol              | Value             | Unit             |
|---|---------------------|-------------------|------------------|
| Repetitive peak off-state voltage   | V <sub>DRM</sub>    | 600 / 800         | V                |
| Repetitive peak reverse voltage   | V <sub>RRM</sub>    | 600 / 800         | V                |
| RMS on-state current  | I <sub>T(RMS)</sub> | 6                 | A                |
| Non repetitive surge peak on-state current (full cycle, F=50Hz)                   | I <sub>TSM</sub>    | 60                | A                |
| I <sup>2</sup> t value for fusing (tp=10ms)                                       | I <sup>2</sup> t    | 21                | A <sup>2</sup> s |
| Critical rate of rise of on-state current (I <sub>G</sub> = 2 × I <sub>GT</sub> ) | di <sub>T</sub> /dt | I - II - III   50 | A/μs             |
| Peak gate current   | I <sub>GM</sub>     | 4                 | A                |
| Average gate power dissipation  | P <sub>G(AV)</sub>  | 1                 | W                |
| Junction Temperature  | T <sub>J</sub>      | -40 ~ +125        | °C               |
| Storage Temperature   | T <sub>STG</sub>    | -40 ~ +150        | °C               |

### Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

| Parameter                                    | Symbol               | Test Condition   | Value                  |       | Unit   |       |      |
|--|----------------------|--|------------------------|-------|--------|-------|------|
|  |                      |  | SW                     | CW    |        |       |      |
| Gate trigger current                         | I <sub>GT</sub>      | V <sub>D</sub> = 12V R <sub>L</sub> = 33Ω                                | I - II - III           | ≤ 10  | ≤ 35   | mA    |      |
| Gate trigger voltage                         | V <sub>GT</sub>      | T <sub>J</sub> = 25°C  | I - II - III           | ≤ 1.3 |        | V     |      |
| Gate non-trigger voltage                     | V <sub>GD</sub>      | V <sub>D</sub> = V <sub>DRM</sub> T <sub>J</sub> = 125°C                 |                        |       | ≥ 0.2  | V     |      |
| latching current                             | I <sub>L</sub>       | I <sub>G</sub> = 1.2I <sub>GT</sub>                                      | I - III                | ≤ 25  | ≤ 50   | mA    |      |
|  |                      |  | II                     | ≤ 30  | ≤ 60   |       |      |
| Holding current                              | I <sub>H</sub>       | I <sub>T</sub> = 100mA   |                        |       | ≤ 15   | ≤ 35  | mA   |
| Critical-rate of rise of commutation voltage | dV <sub>D</sub> /dt  | V <sub>D</sub> = 2/3V <sub>DRM</sub><br>Gate Open T <sub>J</sub> = 125°C |                        |       | ≥ 40   | ≥ 400 | V/μs |
| <b>STATIC CHARACTERISTICS</b>                |                      |  |                        |       |        |       |      |
| Forward "on" voltage                         | V <sub>TM</sub>      | I <sub>TM</sub> = 8.5 A tp = 380μs                                       |                        |       | ≤ 1.55 | V     |      |
| Repetitive Peak Off-State Current            | I <sub>DRM</sub>     | V <sub>D</sub> = V <sub>DRM</sub> V <sub>R</sub> = V <sub>RRM</sub>      | T <sub>J</sub> = 25°C  | ≤ 5   |        | μA    |      |
| Repetitive Peak Reverse Current              | I <sub>RRM</sub>     |  | T <sub>J</sub> = 125°C | ≤ 1   |        | mA    |      |
| <b>THERMAL RESISTANCES</b>                   |                      |  |                        |       |        |       |      |
| Thermal resistance                           | R <sub>th(j-c)</sub> | Junction to case(AC)   |                        |       | 2.5    | °C/W  |      |
|  | R <sub>th(j-a)</sub> | Junction to ambient  |                        |       | 60     | °C/W  |      |

**Typical Characteristics**

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

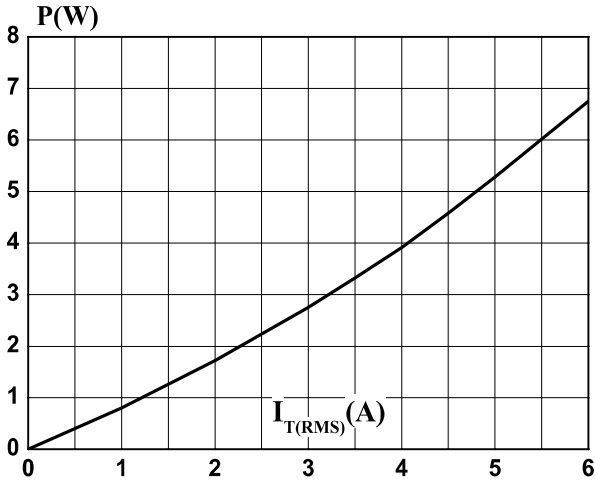


FIG.2: RMS on-state current versus case temperature (full cycle)

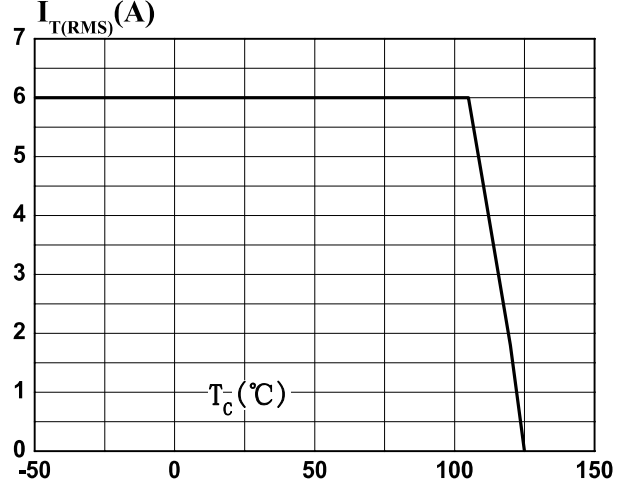


FIG.3: Surge peak on-state current versus number of cycles

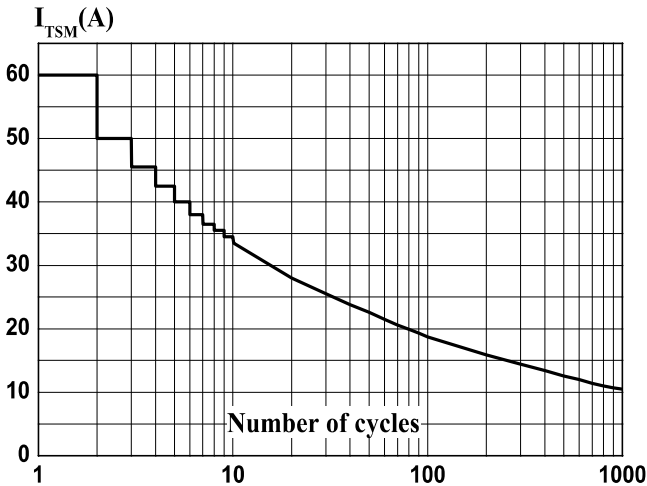


FIG.4: On-state characteristics (maximum values)

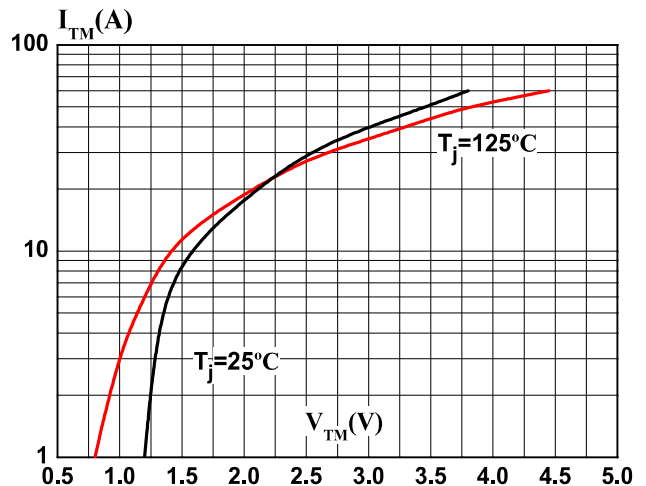


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10ms$

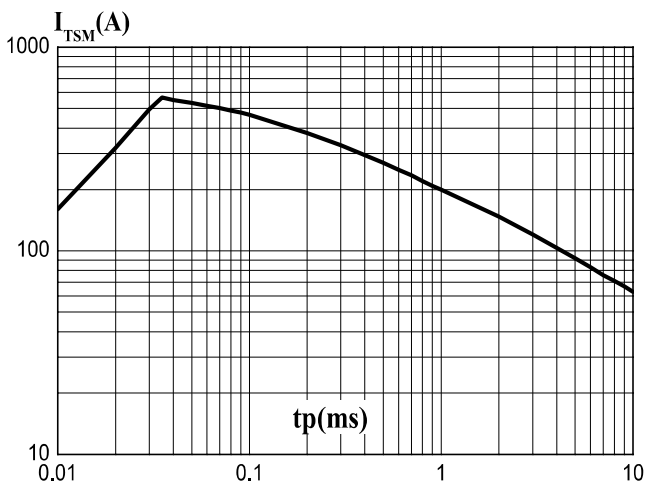
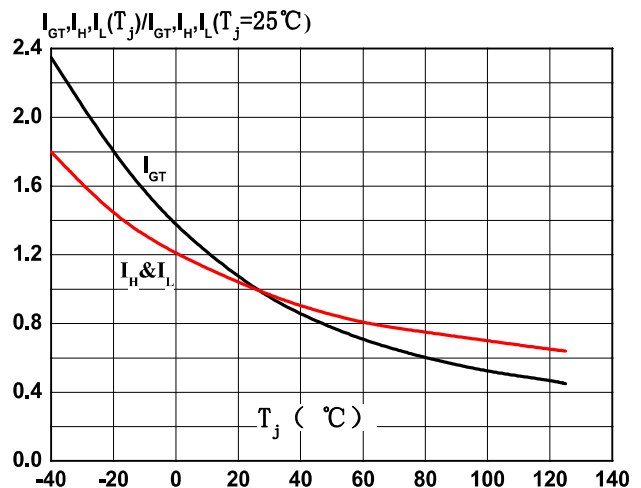
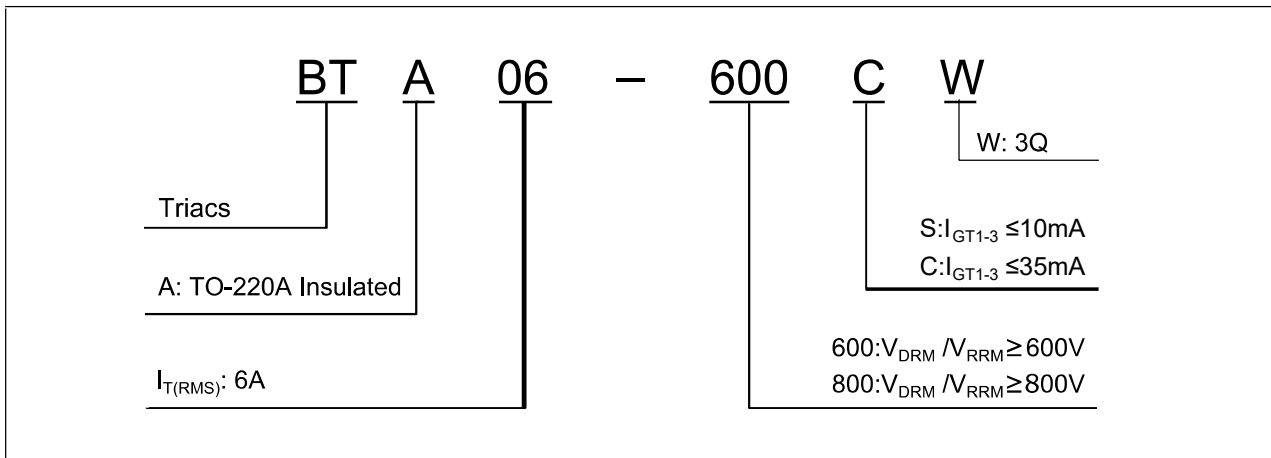


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



**Ordering Information**



**TO-220A Insulated Package Information**

